

International Rectifier

Features

- Output Power MOSFETs in half-bridge configuration
- 500V Rated Breakdown Voltage
- High side gate drive designed for bootstrap operation
- Matched propagation delay for both channels
- Independent high and low side output channels
- Undervoltage lockout
- 5V Schmitt-triggered input logic
- Half-Bridge output out of phase with AIN

Description

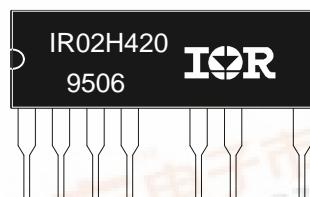
The IR02H420 is a high voltage, high speed half bridge. Proprietary HVIC and latch immune CMOS technologies, along with the HEXFET® power MOSFET technology, enable ruggedized single package construction. The logic inputs are compatible with standard CMOS or LSTTL outputs. The front end features an independent high and low side driver in phase with the logic compatible input signals. The output features two HEXFETs in a half-bridge configuration with a high pulse current buffer stage designed for minimum cross-conduction in the half-bridge. Propagation delays for the high and low side power MOSFETs are matched to simplify use. The device can operate up to 500 volts.

HIGH VOLTAGE HALF-BRIDGE

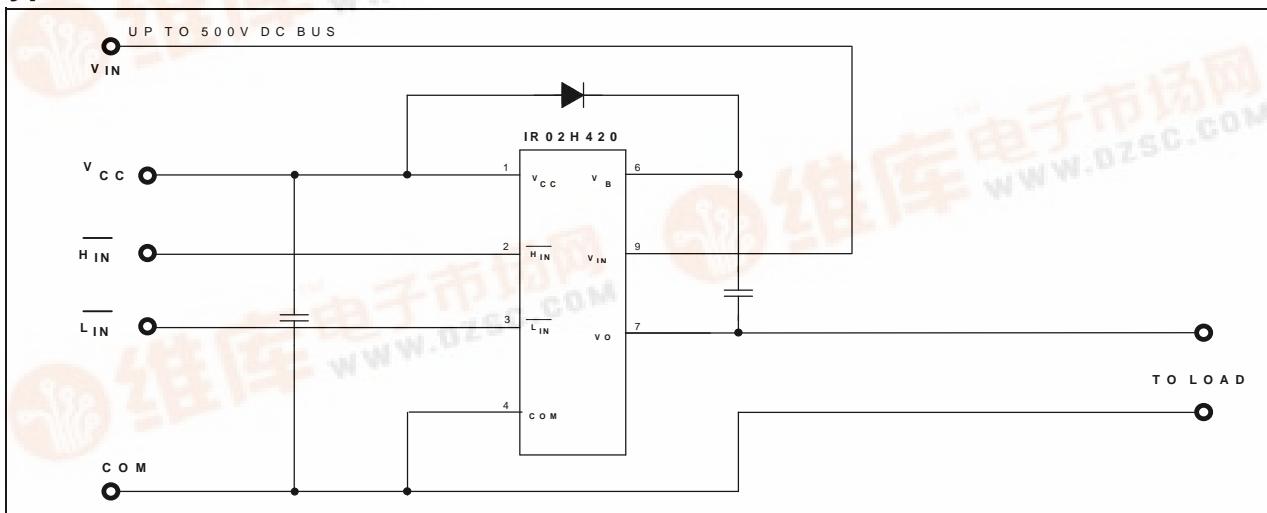
Product Summary

V_{IN} (max)	500V
$t_{on/off}$	130 ns
t_{rr}	270 ns
$R_{DS(on)}$	3.0 Ω
P_D ($T_A = 25^\circ C$)	2.0W

Package



Typical Connection



Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

Symbol	Parameter Definition	Min.	Max.	Units
V_{IN}	High Voltage Supply	-0.3	500	V
V_B	High Side Floating Supply Absolute Voltage	-0.3	525	
VO	Half-Bridge Output Voltage	-0.3	$V_{IN} + 0.3$	
V_{IH}/V_{IL}	Logic Input Voltage (HIN & LIN)	-0.3	$V_{CC} + 0.3$	
V_{CC}	Low Side and Logic Fixed Supply Voltage	-0.3	25	
dv/dt	Peak Diode Recovery dv/dt	---	3.5	V/ns
P_D	Package Power Dissipation @ $T_A \leq +25^\circ\text{C}$	---	2.00	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	---	60	$^\circ\text{C}/\text{W}$
T_J	Junction Temperature	-55	150	$^\circ\text{C}$
T_S	Storage Temperature	-55	150	
T_L	Lead Temperature (Soldering, 10 seconds)	---	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions.

Symbol	Parameter Definition	Min.	Max.	Units
V_B	High Side Floating Supply Absolute Voltage	$VO + 10$	$VO + 20$	V
V_{IN}	High Voltage Supply	---	500	
VO	Half-Bridge Output Voltage	(note 1)	500	
V_{CC}	Low Side and Logic Fixed Supply Voltage	10	20	
V_{IH}/V_{IL}	Logic Input Voltage (HIN & LIN)	0	V_{CC}	
I_D	Continuous Drain Current ($T_A = 25^\circ\text{C}$)	---	0.7	A
	($T_A = 85^\circ\text{C}$)	---	0.5	
T_A	Ambient Temperature	-40	125	$^\circ\text{C}$

Note 1: Logic operational for VO of -5 to 500 V. Logic state held for VO of -5 to $-V_B$.

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC} , V_B) = 15V and T_A = 25°C unless otherwise specified. Switching time waveform definitions are shown in figure 2.

Symbol	Parameter Definition	$T_A = 25^\circ C$			Units	Test Conditions
		Min.	Typ.	Max.		
t_{on}	Turn-On Propagation Delay (see note 2)	---	130	200	ns	$V_S = 0 V$
t_{off}	Turn-Off Propagation Delay (see note 2)	---	90	200		$V_S = 500 V$
t_r	Turn-On Rise Time (see note 2)	---	80	120		
t_f	Turn-Off Fall Time (see note 2)	---	40	70		
MT	Delay Matching, HS & LS Turn-On/Off	---	30	---		
t_{rr}	Reverse Recovery Time (MOSFET Body Diode)	---	260	---		$I_F = 0.7 A$
Q_{rr}	Reverse Recovery Charge (MOSFET Body Diode)	---	0.7	---	μC	$di/dt = 100A/\mu s$

Note 2: Switching times as specified and illustrated in figure 2 are referenced to the MOSFET gate input voltage. This is shown as HO in figure 2.

Static Electrical Characteristics

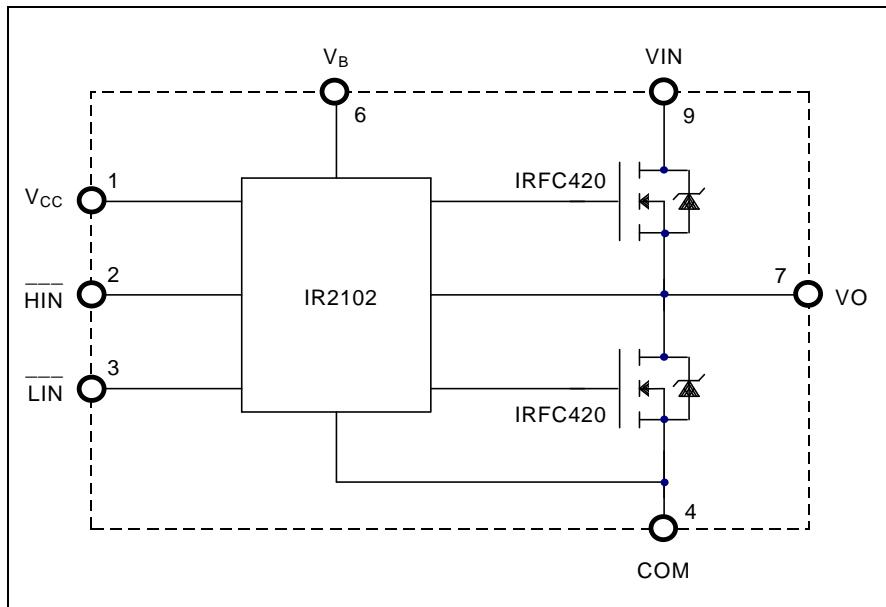
V_{BIAS} (V_{CC} , V_B) = 15V and T_A = 25°C unless otherwise specified. The Input voltage and current levels are referenced to COM.

Symbol	Parameter Definition	$T_A = 25^\circ C$			Units	Test Conditions
		Min.	Typ.	Max.		
Supply Characteristics						
V_{CCUV+}	V_{CC} Supply Undervoltage Positive Going Threshold	8.8	9.3	9.8	V	
V_{CCUV-}	V_{CC} Supply Undervoltage Negative Going Threshold	7.5	8.2	8.6		
I_{QCC}	Quiescent V_{CC} Supply Current	---	140	240	μA	
I_{QBS}	Quiescent V_B Supply Current	---	20	50		
I_{OS}	Offset Supply Leakage Current	---	---	50		$V_B = V_S = 500V$
Input Characteristics						
V_{IH}	Logic "1" Input Voltage	2.7	---	---	V	$V_{CC} = 10V$ to 20V
V_{IL}	Logic "0" Input Voltage	---	---	0.8		
I_{IN+}	Logic "1" Input Bias Current	---	20	40	μA	
I_{IN-}	Logic "0" Input Bias Current	---	---	1.0	μA	
Output Characteristics						
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	---	3.0	---	Ω	$I_D = 700mA$
V_{SD}	Diode Forward Voltage	---	0.8	---	V	$T_j = 150^\circ C$

IR02H420



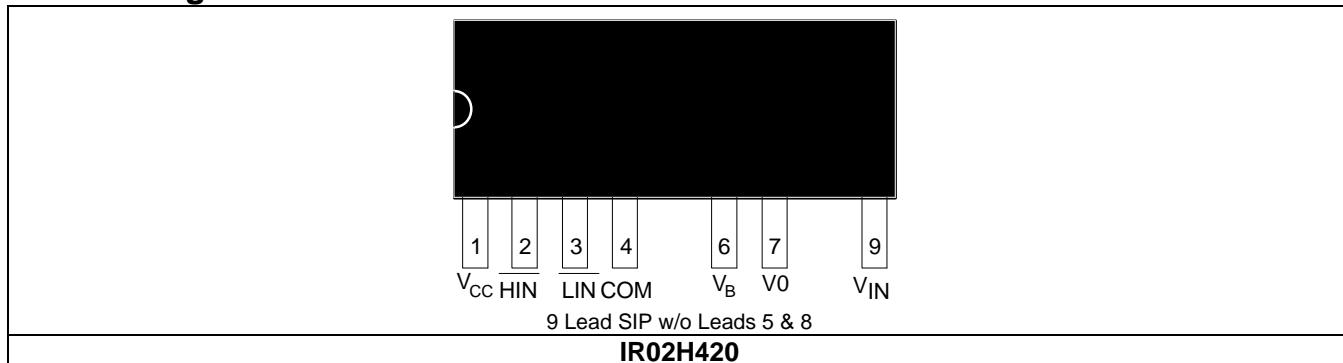
Functional Block Diagram



Lead Definitions

Symbol	Lead Description
V _{CC}	Logic and internal gate drive supply voltage.
HIN	Logic input for high side Half Bridge output, out of phase
LIN	Logic input for low side Half Bridge output, in phase
V _B	High side gate drive floating supply. For bootstrap operation a high voltage fast recovery diode is needed to feed from V _{CC} to V _B .
V _{IN}	High voltage supply.
VO	Half-Bridge output.
COM	Logic and low side of Half-Bridge return.

Lead Assignments



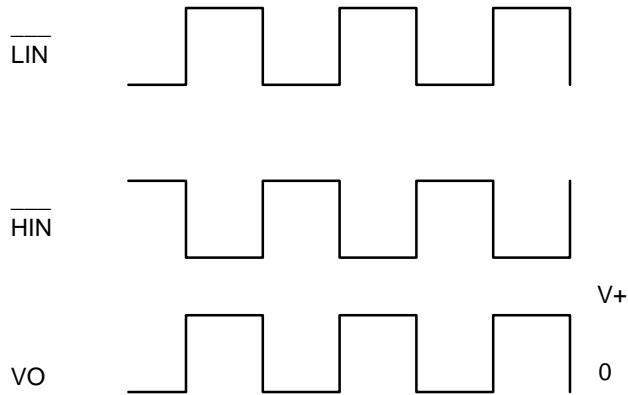


Figure 1. Input/Output Timing Diagram

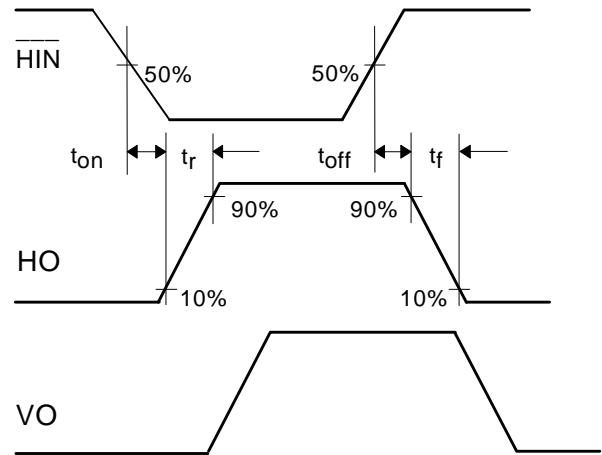


Figure 2. Switching Time Waveform Definitions

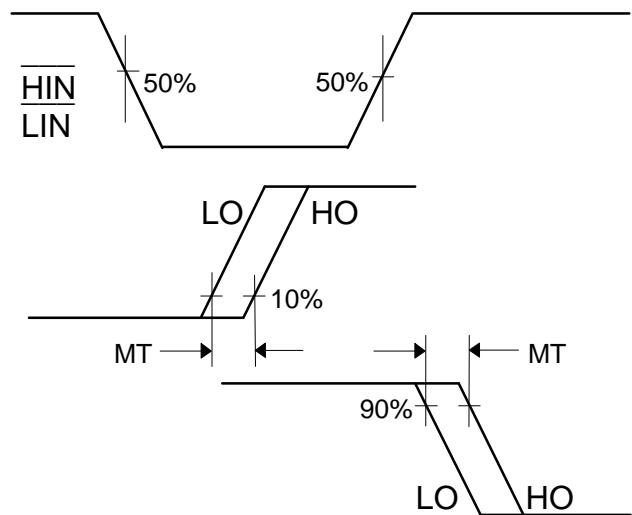
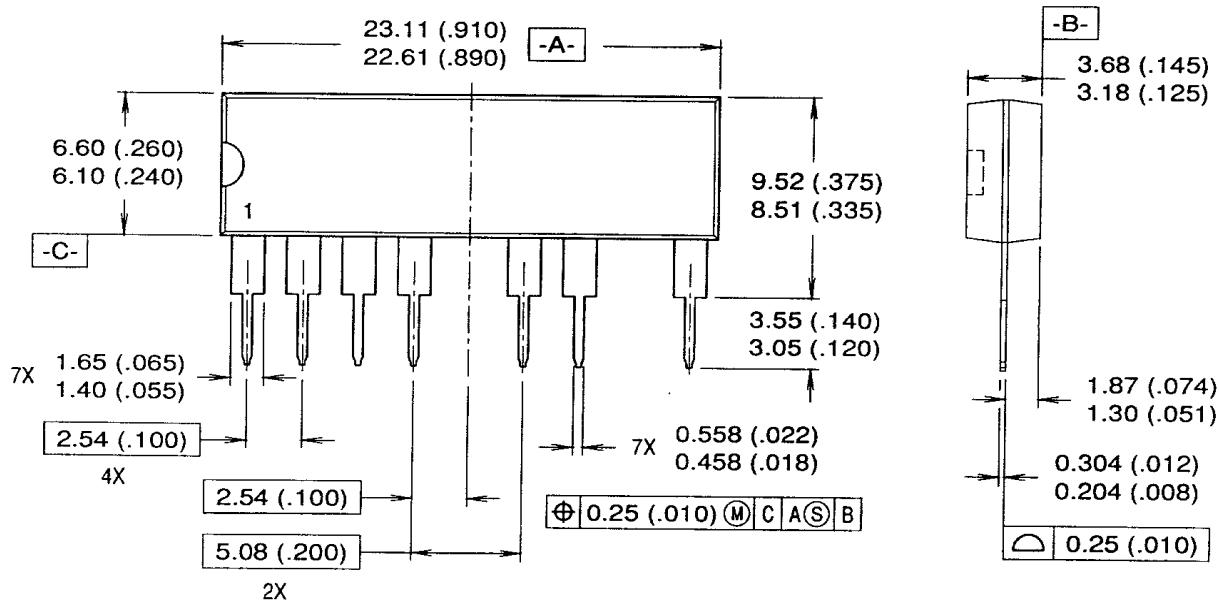


Figure 3. Delay Matching Waveform Definitions

IR02H420



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

Package Outline

International Rectifier

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Data and specifications subject to change without notice.

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